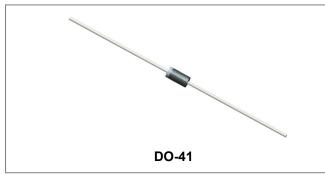






## SF11G-SF18G SUPER FAST RECTIFIER



### **Features**

- Super fast switching for high efficiency
- Low leakage current
- · High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Mechanical Data**

- Case: JEDEC DO-41 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750,Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.012 ounce, 0.34 grams

## Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	SF11G	SF12G	SF13G	SF14G	SF15G	SF16G	SF18G	Units
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	150	200	300	400	600	V
Maximum RMS voltage	V <sub>RMS</sub>	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	150	200	300	400	600	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at $T_A$ =55° $\mathbb{C}$	I <sub>(AV)</sub>	1.0				Α			
Peak forward surge current 8.3ms single half sinewave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	30				А			
Maximum instantaneous forward voltage at 1.0A	V <sub>F</sub>	0.95 1.25 1.7			1.7	V			
Maximum DC reverse current $T_A$ =25 $^{\circ}$ C at rated DC blocking voltage $T_A$ =100 $^{\circ}$ C	I <sub>R</sub>	5.0 50.0			μA				
Maximum Reverse Recovery Time (Note 1)	Trr	35				ns			
Typical Junction Capacitance (Note 2)	C₃	15.0 10.0			pF				
Typical Thermal Resistance (Note 3)	Reja	60.0				°C/W			
Junction Temperature	TJ	-65 to +150				°C			
Storage Temperature Range	T <sub>STG</sub>	-65 to +150			°C				

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A. Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.
  - China Germany Korea Singapore United States
    - http://www.smc-diodes.com
      sales@ smc-diodes.com







## **Ratings and Characteristics Curves**

FIG. 1- FORWARD CURRENT DERATING CURVE

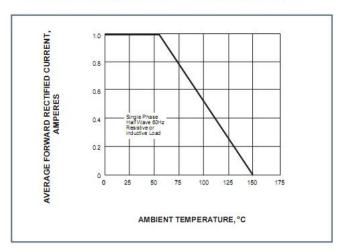


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

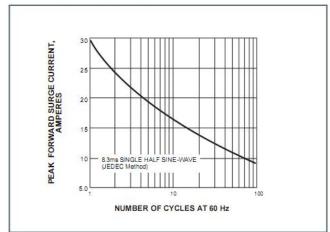
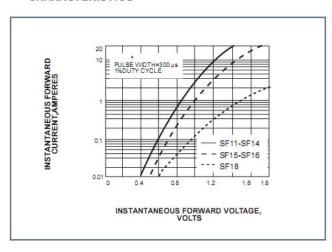
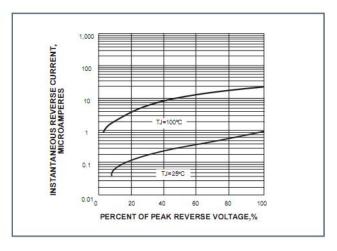


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



#### FIG. 4-TYPICAL REVERSE CHARACTERISTICS



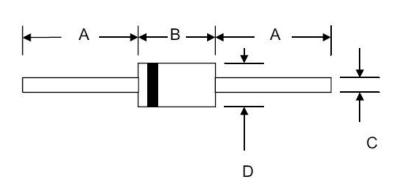
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## **Mechanical Dimensions DO-41**



CYMPOL	Millim	neters	Inches			
SYMBOL	Min.	Max.	Min.	Max.		
Α	25.4	-	1.000	-		
В	4.06	5.21	0.160	0.205		
С	0.70	0.90	0.028	0.034		
D	2.00	2.72	0.079	0.107		

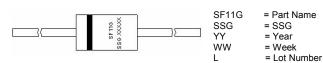
## **Ordering Information**

Device	Package	Shipping
SF11G		
THRU	DO-41 (Pb-Free)	5000pcs /Tape
SF18G	, , ,	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**

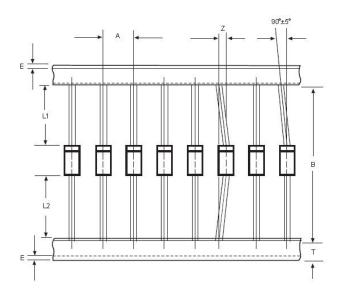
Where XXXXX is YYWWL



Cautions: Molding resin

Epoxy resin UL:94V-0

# **Carrier Tape Specification DO-41**



SYMBOL	Millimeters			
	Min.	Max.		
А	4.50	5.50		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
E	-	0.80		
IL1-L2I	-	1.0		

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